Signetics

Linear Products

DESCRIPTION

The NE/SE5539 is a very wide bandwidth, high slew rate, monolithic operational amplifier for use in video amplifiers, RF amplifiers, and extremely high slew rate amplifiers.

Emitter-follower inputs provide a true differential high input impedance device. Proper external compensation will allow design operation over a wide range of closed-loop gains, both inverting and non-inverting, to meet specific design requirements.

NE/SE5539 High Frequency Operational Amplifier

Product Specification

FEATURES

Bandwidth

- Unity gain 350MHz
- Full power 48MHz
- GBW 1.2 GHz at 17dB
- Slew rate: 600/Vµs
- A_{VOL}: 52dB typical
- Low noise 4nV/VHz typical
- MIL-STD processing available

APPLICATIONS

- High speed datacomm
- Video monitors & TV
- Satellite communications
- Image processing
- RF instrumentation & oscillators
- Magnetic storage
- Military communications

ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE
14-Pin Plastic DIP	0 to +70°C	NE5539N
14-Pin Plastic SO	0 to +70°C	NE5539D
14-Pin Cerdip	0 to +70°C	NE5539F
14-Pin Plastic DIP	-55°C to +125°C	SE5539N
14-Pin Cerdip	~55°C to +125°C	SE5539F

ABSOLUTE MAXIMUM RATINGS¹

SYMBOL	PARAMETER	RATING	UNIT
V _{CC}	Supply voltage	± 12	V
PDMAX	Maximum power dissipation, $T_A = 25^{\circ}C (still-air)^2$ F package N package D package	1.17 1.45 0.99	× × ×
T _{STG}	Storage temperature range	-65 to +150	°C
TJ	Max junction temperature	150	°C
T _A	Operating temperature range NE SE	0 to 70 -55 to +125	°C °C
T _{SOLD}	Lead temperature (10sec max)	300	°C

NOTES:

 Differential input voltage should not exceed 0.25V to prevent excessive input bias current and common-mode voltage 2.5V. These voltage limits may be exceeded if current is limited to less than 10mA.

2. Derate above 25°C, at the following rates:

F package at 9.3 mW/°C

N package at 11.6 mW/°C

D package at 7.9 mW/°C

PIN CONFIGURATION



NE/SE5539

EQUIVALENT CIRCUIT



DC ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 8V$, $T_A = 25^{\circ}C$, unless otherwise specified.

				SE553	9					
SYMBOL	PARAMETER	TEST CONDITIONS			Тур	Max	Min	Тур	Max	UNIT
Mar		V 0V D 4000	Over temp		2	5				
vos ∣	OS Input onset voltage	$v_0 = 0v, H_s = 100sz$	T _A = 25°C		2	3		2.5	5	
	$\Delta V_{OS} / \Delta T$				5	{		5		μV/°C
los	Input offset current		Over temp		0.1	3				
			T _A = 25°C		0.1	1			2	?
	$\Delta I_{OS} / \Delta T$				0.5			0.5		nA/°C
	Input bias current		Over temp	5	6	25				
18			T _A = 25°C		5	13		5	20	
	$\Delta I_{B} / \Delta T$				10			10		nA/°C
CMRR	Common-mode rejection ratio	$F = 1 \text{ kHz}, R_{S} = 100 \Omega, T$	V _{CM} ± 1.7V	70	80		70	80	,	dB
			Over temp	70	80					dB
R _{IN}	Input impedance				100			100		kΩ
ROUT	Output impedance				10			10		Ω

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SYMBOL	PARAMETER	TES	TEST CONDITIONS			Тур	Max	Min	Тур	Max	UNIT
		$R_L = 150\Omega$ to	GND and	+ Swing				+ 2.3	+ 2.7		~~~
VOUT	Output voltage swing	470Ω to	-V _{CC}	-Swing				-1.7	-2.2		v
			0.000	+ Swing	+ 2.3	+ 3.0					
N.	Output voltage ewing	$R_L = 2k\Omega$ to	Over temp	-Swing	-1.5	-2.1					•
	OUT Output voltage swing GND GND	T - 05%0	+ Swing	+ 2.5	+3.1						
		1	$I_{A} = 25^{\circ}C$	-Swing	-2.0	-2.7		1			v
	Desitive supply supprt	$V_0 = 0, R_1 = \infty$		Over temp		14	18				— mA
'cc+	I _{CC} + Positive supply current			T _A = 25°C		14	17		14	18	
		V - 0.5				11	15				
ICC-	Negative supply current	$v_0 = 0, F$	-1 ₁ = ∞	T _A = 25°C		11	14		11	15	
	Davies averte scienting estin	A)/	+ 1)/	Over temp		300	1000				
PSRR	Power supply rejection ratio		$\Delta V_{CC} = \pm 1V$ $T_A =$		l				200	1000	μν/ν
A _{VOL}	Large signal voltage gain	V_0 $R_L = 150\Omega$	V_{O} = +2.3V, -1.7V R _L = 150 Ω to GND, 470 Ω to -V _{CC}					47	52	57	dB
		$V_{0} = +2.3V_{0}$	√, −1.7V								dD
AVOL	Large signal voltage gain	$R_L = 2\Omega$ to GND		T _A = 25°C	{			47	52	57	08
		$V_{\rm O} = +2.5^{\rm V}$	$V_{\rm O} = +2.5V_{\rm V} - 2.0V$		46		60				٩D
AVOL	Large signal voltage gain	$R_L = 2k\Omega$ to GND		T _A = 25°C	48	53	58]			uB

DC ELECTRICAL CHARACTERISTICS (Continued) $V_{CC} = \pm 8V$, $T_A = 25^{\circ}C$, unless otherwise specified.

DC ELECTRICAL CHARACTERISTICS $V_{CC} \approx \pm 6V$, $T_A = 25^{\circ}C$, unless otherwise specified.

						SE5539			
SYMBOL	PARAMETER	TEST C	Min	Тур	Max	UNIT			
			(2	5		
VOS	input onset voltage		T _A = 25°C		2	3	mv		
1.00				Over temp		0.1	3		
'OS				T _A = 25°C		0.1	1	μΑ	
le.	La laput biog ourroot			Over temp		5	20	Δ	
'B				T _A = 25°C		4	10	μη	
CMRR	Common-mode rejection ratio	$V_{CM} = \pm 1.3V$, $R_S = 100\Omega$			70	85		dB	
	Positivo supply ourropt			Over temp		11	14	m۵	
				$T_A = 25^{\circ}C$		11	13		
lee-	Negative supply current	Over tem		Over temp		8	_11	mA	
-00-				T _A = 25°C		8	10		
DCDD	Power supply rejection ratio	()/ = + 1	V	Over temp		300	1000		
Fonn			•	T _A = 25°C				μ•/ •	
			Over temp	+ Swing	+1.4	+ 2.0			
		$R_L \approx 150\Omega$ to GND	Over temp	-Swing	-1.1	-1.7			
VOUT	Culput voltage swing	and 390 Ω to -V_{CC}	T - 25%	+ Swing	+ 1.5	+ 2.0			
			14 - 25 C	-Swing	-1.4	-1.8			

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AC ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 8V$, $R_L = 150\Omega$ to $GND \& 470\Omega$ to $-V_{CC}$, unless otherwise specified.

	PARAMETER TEST		SE5539						
STMBUL		TEST CONDITIONS	Min	Тур	Max	Min	Тур	Max	UNIT
BW	Gain bandwidth product	$A_{CL} = 7, V_0 = 0.1 V_{P-P}$		1200			1200		MHz
	Small-signal bandwidth	$A_{CL} = 2, R_{L} = 150\Omega^{1}$		110			110		MHz
ts	Settling time	$A_{CL} = 2, R_{L} = 150\Omega^{1}$		15			15		ns
SR	Slew rate	$A_{CL} \approx 2$, $R_L = 150\Omega^1$		600			600		V∕µs
teD	Propagation delay	$A_{CL} = 2, R_{L} = 150\Omega^{1}$		7			7		ns
	Full power response	$A_{CL} = 2, R_{L} = 150\Omega^{1}$		48			48	{	MHz
	Full power response	$A_V = 7, R_L = 150\Omega^1$		20			20		MHz
	Input noise voltage	R _S = 50Ω, 1MHz		4			4		nV/√Hz
	Input noise current	1MHz		6			6		pA/√Hz

NOTE:

1. External compensation.

AC ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 6V$, $R_L = 150\Omega$ to GND and 390Ω to $-V_{CC}$, unless otherwise specified.

SYMBOL	PARAMETER					
		TEST CONDITIONS	Min	Тур	Max	UNIT
BW	Gain bandwidth product	$A_{CL} = 7$		700		MHz
	Small-signal bandwidth	$A_{CL} = 2^1$		120		MHz
ts	Settling time	$A_{CL} = 2^1$		23		ns
SR	Slew rate	$A_{CL} = 2^1$		330		V/µs
tpD	Propagation delay	$A_{CL} = 2^1$		4.5		ns
	Full power response	$A_{CL} = 2^1$		20		MHz

NOTE:

1. External compensation.

TYPICAL PERFORMANCE CURVES



4-227

TYPICAL PERFORMANCE CURVES (Continued)



NE/SE5539

OPTIONAL OFFSET

0-1

CIRCUIT LAYOUT CONSIDERATIONS

As may be expected for an ultra-high frequency, wide-gain bandwidth amplifier, the physi-



cal circuit layout is extremely critical. Breadboarding is not recommended. A doublesided copper-clad printed cirucit board will result in more favorable system operation. An

1nF

example utilizing a 28dB non-inverting amp is shown in Figure 1.

NE/SE5539

Figure 1. 28dB Non-Inverting Amp Sample PC Layout

November 3, 1987

High Frequency Operational Amplifier

NE5539 COLOR VIDEO AMPLIFIER

The NE5539 wideband operational amplifier is easily adapted for use as a color video amplifier. A typical circuit is shown in Figure 2 along with vector-scope¹ photographs showing the amplifier differential gain and phase response to a standard five-step modulated staircase linearity signal (Figures 3, 4 and 5). As can be seen in Figure 4, the gain varies less than 0.5% from the bottom to the top of the staircase. The maximum differential phase shown in Figure 5 is approximately +0.1°.

The amplifier circuit was optimized for a 75Ω input and output termination impedance with a gain of approximately 10 (20dB).

NOTE:

1. The input signal was 200mV and the output 2V. V_{CC} was $\pm\,8V.$



750

22nF

Figure 2. NE5539 Video Amplifier

470

NOTE:

Instruments used for these measurements were Tektronix 146 NTSC test signal generator, 520A NTSC vectorseope, and 1480 waveform monitor.



dB LOSS-

E) ZO = 75

TC08750S

NE/SE5539

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APPLICATIONS



